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**RESPONSE UNDER 37 CFR 1.116  
EXPEDITED PROCEDURE  
EXAMINING GROUP 2766**

**PATENT**  
Attorney Docket No. 99154X204201

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:

Fang et al.

Application No. 09/595,227

Filed: June 16, 2000

Art Unit: 2766

Examiner: Hadi Shakeri

For: METHOD FOR POLISHING A  
MEMORY OR RIGID DISK WITH  
A PHOSPHATE ION-  
CONTAINING POLISHING  
SYSTEM

**PENDING CLAIMS AFTER AMENDMENTS  
MADE IN RESPONSE TO OFFICE ACTION DATED JUNE 13, 2002**

1. A method for planarizing or polishing a surface of a memory disk comprising abrading at least a portion of the surface with a polishing system comprising (i) a polishing composition comprising water, an oxidizing agent, and about 0.04 M or higher phosphate ion or phosphonate ion, and (ii) abrasive material.
2. The method of claim 1, wherein the polishing composition comprises about 0.04 M or higher phosphate ion.
3. The method of claim 1, wherein the polishing composition comprises about 0.04 M or higher phosphonate ion.
4. The method of claim 1, wherein the surface of the memory disk comprises nickel-phosphorus.
5. The method of claim 1, wherein the polishing system has a pH of about 1-12.
6. The method of claim 5, wherein the polishing system has a pH of about 2-5.

7. The method of claim 1, wherein the abrasive material is abrasive particles selected from the group consisting of alumina, silica, titania, ceria, zirconia, germania, magnesia, coformed products thereof, and mixtures thereof.

8. The method of claim 7, wherein the abrasive particles are silica particles.

9. The method of claim 8, wherein the abrasive particles are condensation-polymerized silica particles.

10. The method of claim 1, wherein the abrasive material is abrasive particles present in the polishing composition in a concentration of about 0.1 wt.% or more.

11. The method of claim 1, wherein the abrasive material is fixed on or in a polishing pad.

12. The method of claim 1, wherein the oxidizing agent is selected from the group consisting of per-compounds, bromates, perbromates, chlorates, perchlorates, dichromates, periodates, iodates, nitrates, permanganates, sulfates, citrates, cerium (IV) compounds, oxidizing metal salts, oxidizing metal complexes, nonmetallic oxidizing acids, ferricyanides, trioxides, and salts thereof, and mixtures thereof.

13. The method of claim 12, wherein the oxidizing agent is selected from the group consisting of peroxides, persulfates, percarbonates, and salts thereof, and mixtures thereof.

14. The method of claim 12, wherein the oxidizing agent is selected from the group consisting of hydrogen peroxide, ammonium persulfate, potassium iodate, and mixtures thereof.

15. The method of claim 1, wherein the oxidizing agent is present in the polishing composition in an amount of about 0.01 wt.% or more.

16. The method of claim 15, wherein the oxidizing agent is present in the polishing composition in an amount of about 0.1 wt.% or more.

17. The method of claim 2, wherein the phosphate ion is derived from a water-soluble phosphate.

18. The method of claim 17, wherein the phosphate ion is derived from a source of phosphate ion selected from the group consisting of orthophosphates, polyphosphates, and mixtures thereof.

19. The method of claim 17, wherein the phosphate ion is derived from a source of phosphate ion selected from the group consisting of ammonium phosphate, potassium phosphate, sodium tripolyphosphate, and mixtures thereof.

20. The method of claim 3, wherein the phosphonate ion is derived from a source of phosphonate ion selected from the group consisting of amine-containing phosphonates, imine-containing phosphonates, imide-containing phosphonates, amide-containing phosphonates, phosphonate compounds containing no nitrogen, and mixtures thereof.

21. The method of claim 3, wherein the phosphonate ion is derived from a source of phosphonate ion selected from the group consisting of phosphoacetic acid, 2-aminoethyl dihydrogen phosphate, aminotri-(methylenephosphonic acid), nitrilotris(methylene)triphosphonic acid, 1-hydroxyethylidene-1-diphosphonic acid, and diethylenetriaminepenta-(methylenephosphonic acid), and mixtures thereof.

22. The method of claim 1, wherein the phosphate-ion or phosphonate ion is present in the polishing composition in an amount of about 0.06 M or higher.

23. The method of claim 1, wherein the phosphate-ion or phosphonate ion is present in the polishing composition in an amount of about 0.08 M or higher.